



8N60-MH

Preliminary

Power MOSFET

8.0A, 600V N-CHANNEL POWER MOSFET

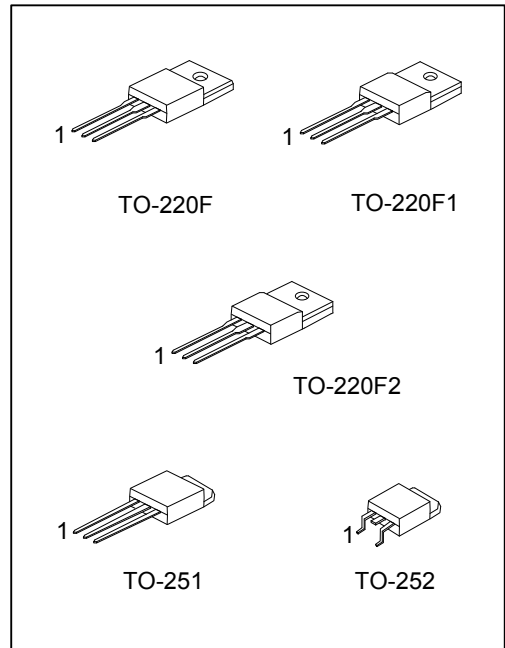
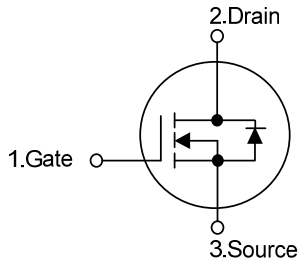
■ DESCRIPTION

The UTC **8N60-MH** is a high voltage power MOSFET combines advanced planar MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

- * $R_{DS(ON)} \leq 1.15 \Omega @ V_{GS}=10V, I_D=4.0A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



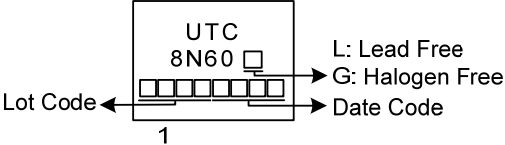
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N60L-TF1-T	8N60G-TF1-T	TO-220F1	G	D	S	Tube
8N60L-TF2-T	8N60G-TF2-T	TO-220F2	G	D	S	Tube
8N60L-TF3-T	8N60G-TF3-T	TO-220F	G	D	S	Tube
8N60L-TM3-T	8N60G-TM3-T	TO-251	G	D	S	Tube
8N60L-TN3-R	8N60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8N60G-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F</p> <p>TM3: TO-251, TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	8	A
Pulsed Drain Current (Note 2)		I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	259	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.3	V/ns
Power Dissipation	TO-220F/TO-220F1	P_D	36	W
	TO-220F2			
	TO-251/TO-252		54	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 7.2\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 8.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F/TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1	θ_{JC}	3.47	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		2.31 (Note)	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

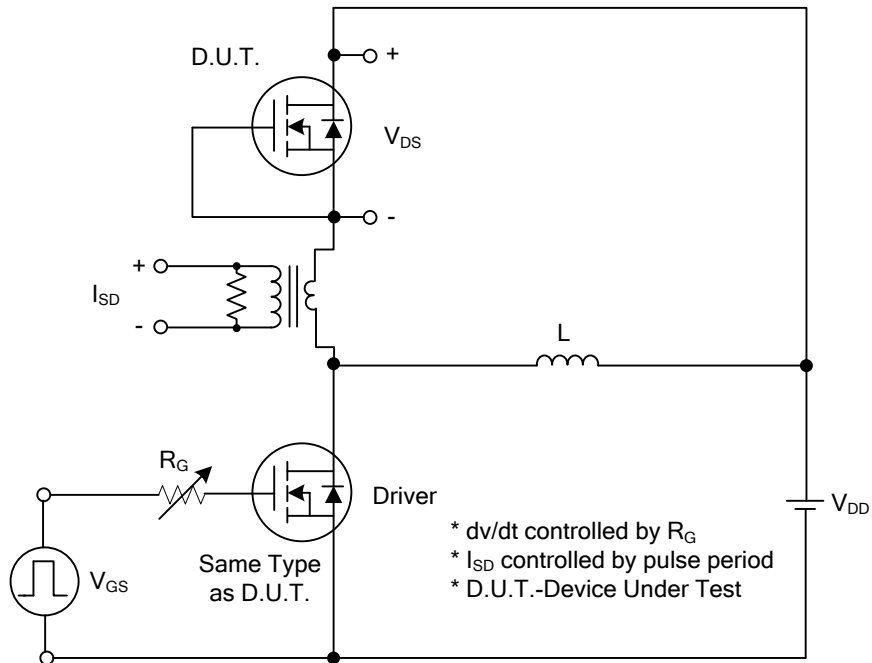
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS} V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4.0A			1.15	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		1020		pF
Output Capacitance	C _{OSS}			130		pF
Reverse Transfer Capacitance	C _{RSS}			18		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =480V, V _{GS} =10V, I _D =8A I _G =1mA (Note 1, 2)		32		nC
Gate-Source Charge	Q _{GS}			7		nC
Gate-Drain Charge	Q _{GD}			12		nC
Turn-On Delay Time (Note 1)	t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =8A, R _G =25Ω (Note 1, 2)		14		ns
Turn-On Rise Time	t _R			20		ns
Turn-Off Delay Time	t _{D(OFF)}			100		ns
Turn-Off Fall Time	t _F			48		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Body-Diode Continuous Current	I _S				8	A
Maximum Body-Diode Pulsed Current	I _{SM}				16	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	I _S =8A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)	t _{rr}	I _S =8A, V _{GS} =0V di/dt=100A/μs		520		ns
Reverse Recovery Charge	Q _{rr}				12	

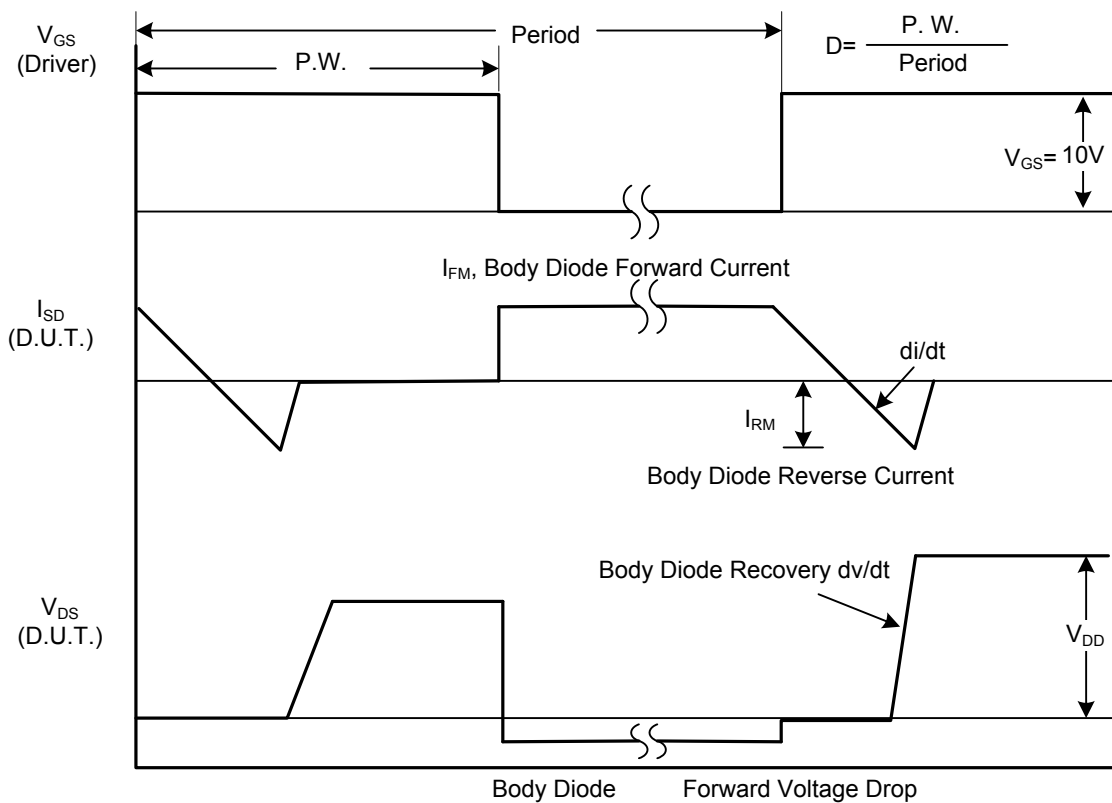
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

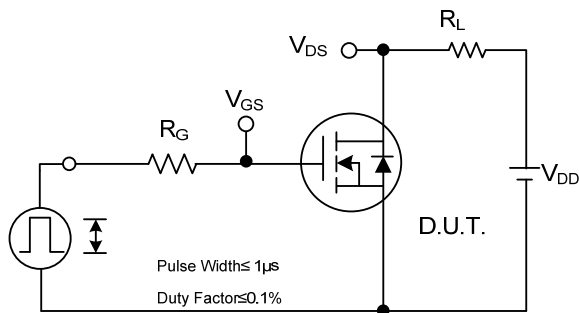


Peak Diode Recovery dv/dt Test Circuit

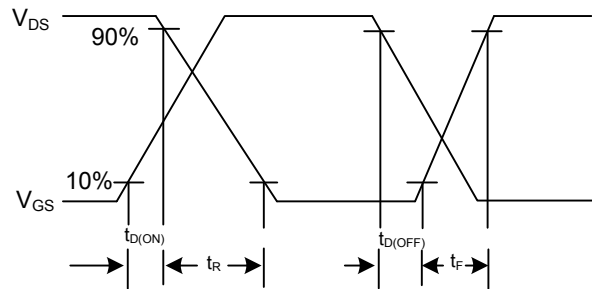


Peak Diode Recovery dv/dt Waveforms

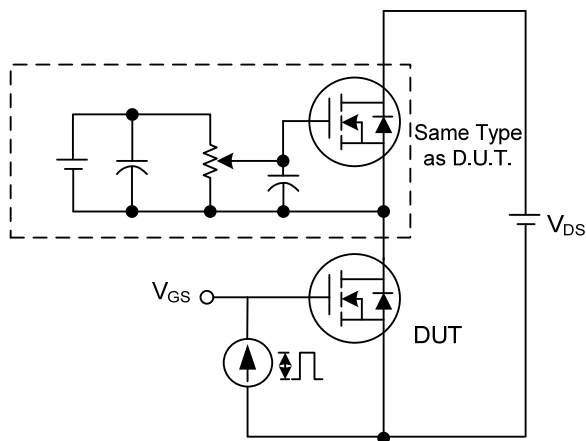
■ TEST CIRCUITS AND WAVEFORMS



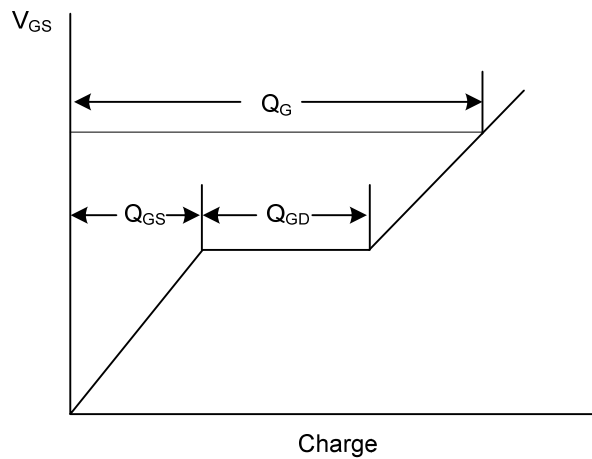
Switching Test Circuit



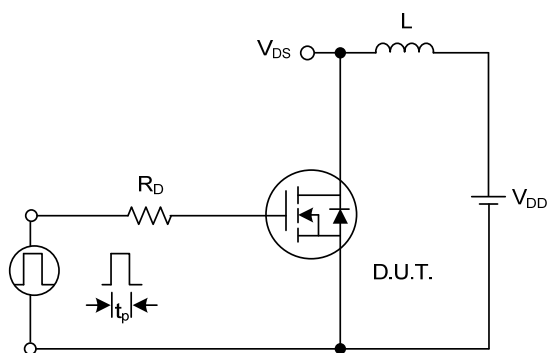
Switching Waveforms



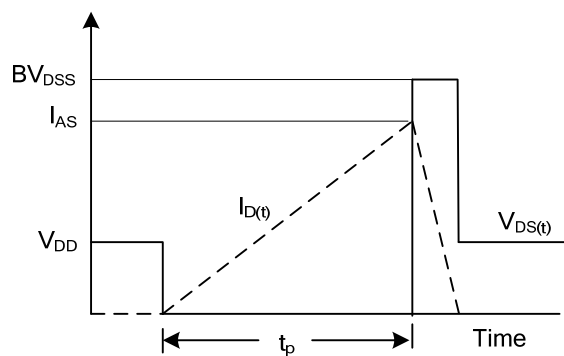
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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